Carrier relaxation mechanisms in self-assembled (In,Ga)As/GaAs quantum dots: Efficient $P \rightarrow S$ Auger relaxation of electrons

II. CHARACTERISTIC DYNAMICAL PROCESSES OF EXCITED ELECTRONS AND HOLES IN SELF-ASSEMBLED (In,Ga)As/GaAs QUANTUM DOTS

A. Barrier-to-wetting layer carrier capture

B. Carrier capture from the wetting layer into the dot

[illegible]

C. Relaxation of excited carriers within the dot

[illegible]

[illegible] [32] [illegible] [33–36] [illegible] [37–40] [illegible]

D. Thermal escape of carriers from dot

[illegible]

[illegible] $_1(0) = {}_2(0)$

[illegible]

D. Comparison to other calculations for (In,Ga)As/GaAs dots

[illegible]

[8] E. A. [illegible], A. D. A[illegible], [illegible] C[illegible] [illegible] E (A[illegible]) **26**, 105 (2005).

[9] E. A. [illegible], [illegible] B[illegible], [illegible] D. A. C[illegible], [illegible] C[illegible] [illegible] B **70**, 161305 [illegible] (2004).

[10] E. A. [illegible], [illegible] B[illegible], [illegible] D. A. C[illegible], [illegible]